



STFI13NK60Z

N-channel 600 V, 0.48 Ω , 13 A, Zener-protected SuperMESH™ Power MOSFET in I²PAKFP package

Datasheet — production data

Features

Order code	V _{DSS}	R _{DS(on)} max	I _D	P _{TOT}
STFI13NK60Z	600 V	<0.55 Ω	13 A	35 W

- Fully insulated and low profile package with increased creepage path from pin to heatsink plate
- Gate charge minimized
- Very low intrinsic capacitance

Applications

- Switching applications

Description

This device is an N-channel Zener-protected Power MOSFET developed using STMicroelectronics' SuperMESH™ technology, achieved through optimization of ST's well established strip-based PowerMESH™ layout. In addition to a significant reduction in on-resistance, this device is designed to ensure a high level of dv/dt capability for the most demanding applications.

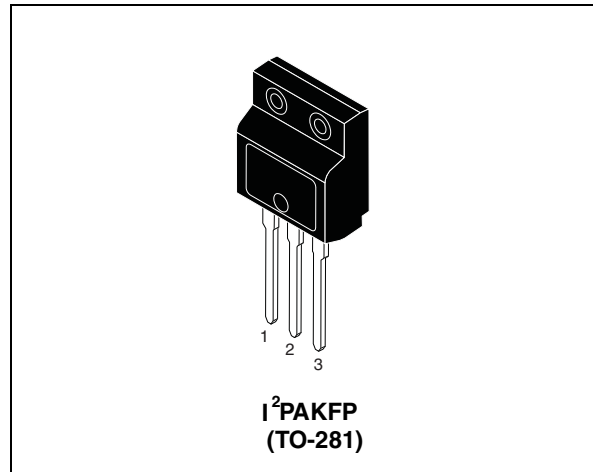


Figure 1. Internal schematic diagram

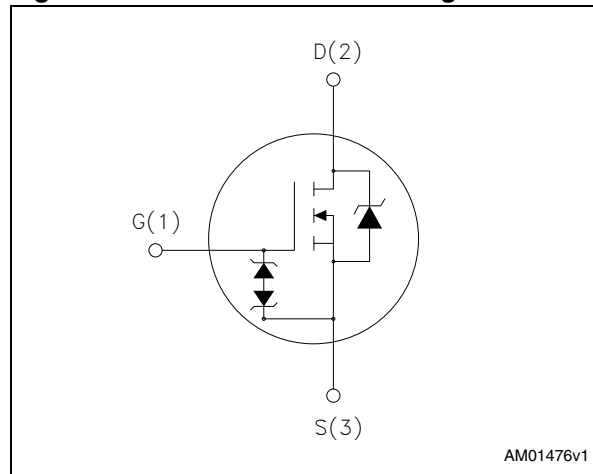


Table 1. Device summary

Order code	Marking	Package	Packaging
STFI13NK60Z	13NK60Z	I ² PAKFP (TO-281)	Tube

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves)	6
3	Test circuits	9
4	Package mechanical data	10
5	Revision history	12

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	600	V
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ °C}$	13 ⁽¹⁾	A
I_D	Drain current (continuous) at $T_C = 100\text{ °C}$	8.2 ⁽¹⁾	A
$I_{DM}^{(2)}$	Drain current (pulsed)	52 ⁽¹⁾	A
P_{TOT}	Total dissipation at $T_C = 25\text{ °C}$	35	W
ESD	Gate-source human body model (R=1,5 k Ω , C=100 pF)	4	kV
dv/dt ⁽³⁾	Peak diode recovery voltage slope	4.5	V/ns
V_{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s; $T_C=25\text{ °C}$)	2500	V
T_j T_{stg}	Operating junction temperature Storage temperature	-55 to 150	$^{\circ}\text{C}$

1. Limited by maximum junction temperature.
2. Pulse width limited by safe operating area.
3. $I_{SD} < 13\text{ A}$, $di/dt < 200\text{ A}/\mu\text{s}$, $V_{DD} = 80\% V_{(BR)DSS}$.

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case Max	3.6	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-amb Max	62.5	$^{\circ}\text{C}/\text{W}$

Table 4. Avalanche characteristics

Symbol	Parameter	Max value	Unit
I_{AR}	Repetitive or non repetitive avalanche current	10 ⁽¹⁾	A
E_{AS}	Single pulse avalanche energy (starting $T_j=25\text{ °C}$, $I_D=I_{AR}$, $V_{DD}=50\text{ V}$)	400	mJ

1. Limited by maximum junction temperature

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified).

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 600\text{ V}$, $V_{DS} = 600\text{ V}$, $T_c = 125\text{ °C}$			1 50	μA μA
I_{GSS}	Gate body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}$, $I_D = 4.5\text{ A}$		0.48	0.55	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 8\text{ V}$, $I_D = 5\text{ A}$	-	11		S
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0$	-	2030 210 48		pF pF pF
$C_{oss\text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0$, $V_{DS} = 0\text{ to }480\text{ V}$	-	125		pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480\text{ V}$, $I_D = 10\text{ A}$ $V_{GS} = 10\text{ V}$ (see Figure 16)	-	66 11 33	92	nC nC nC

1. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time Rise time	$V_{DD}=300\text{ V}$, $I_D=5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 15)	-	22 14	-	ns ns
$t_{d(off)}$ t_f	Turn-off delay time Fall time	$V_{DD}=300\text{ V}$, $I_D=5\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 15)	-	61 12	-	ns ns
$t_{r(Voff)}$ t_f t_c	Off-voltage rise time Fall time Cross-over time	$V_{DD}=480\text{ V}$, $I_D=10\text{ A}$, $R_G=4.7\ \Omega$, $V_{GS}=10\text{ V}$ (see Figure 15)	-	10 9 20	-	ns ns ns

Table 8. Gate-source Zener diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage ($I_D=0$)	$I_{gs}=\pm 1\text{ mA}$	30	-	-	V

The built-in back-to-back Zener diodes have specifically been designed to enhance not only the device's ESD capability, but also to make them safely absorb possible voltage transients that may occasionally be applied from gate to source. In this respect the Zener voltage is appropriate to achieve an efficient and cost-effective intervention to protect the device's integrity. These integrated Zener diodes thus avoid the usage of external components.

Table 9. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		10 40	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD}=10\text{ A}$, $V_{GS}=0$	-		1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}=10\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$, $V_{DD}=35\text{ V}$, $T_J=150\text{ }^\circ\text{C}$	-	570 4.5 16		ns μC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

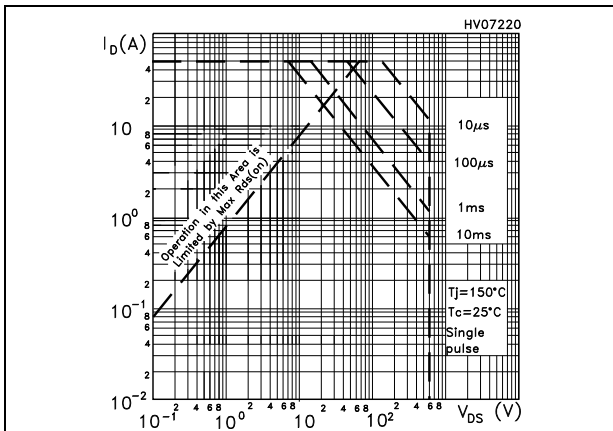


Figure 3. Thermal impedance

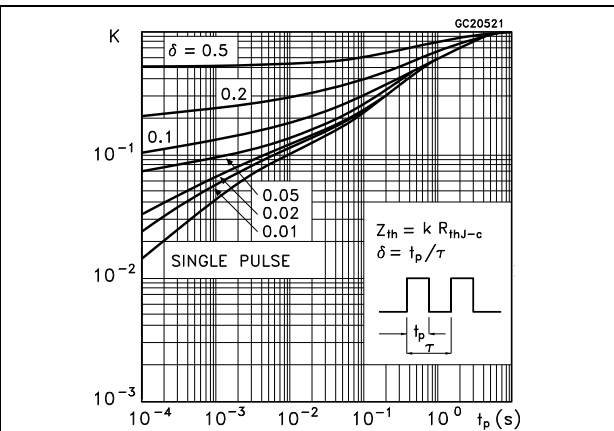


Figure 4. Output characteristics

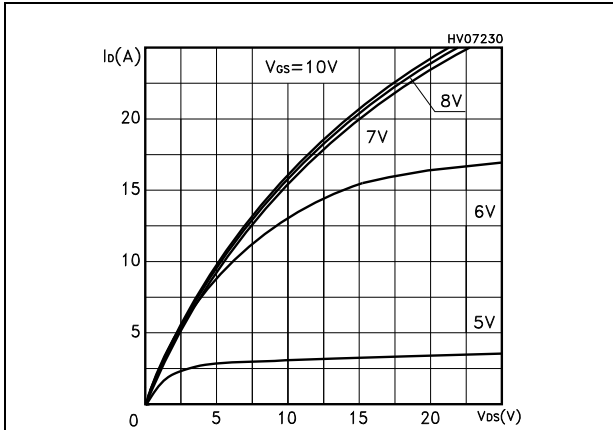


Figure 5. Transfer characteristics

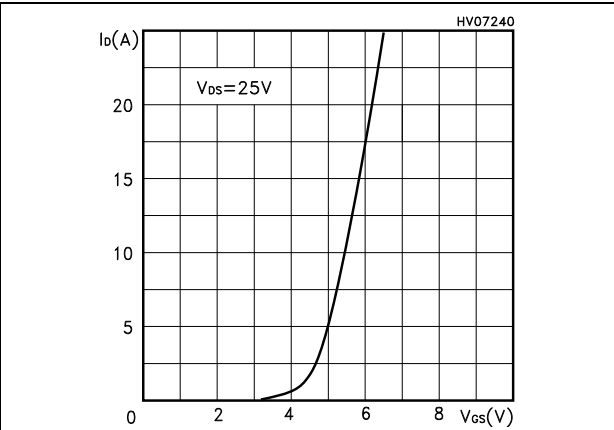


Figure 6. Transconductance

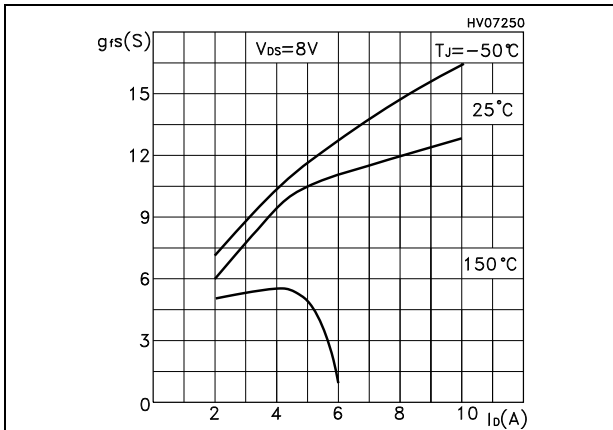


Figure 7. Static drain-source on resistance

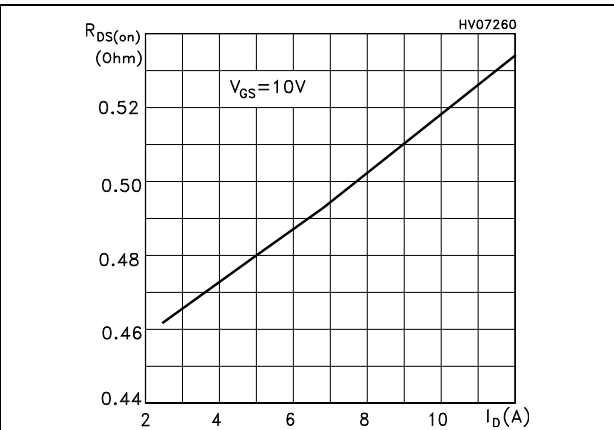


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

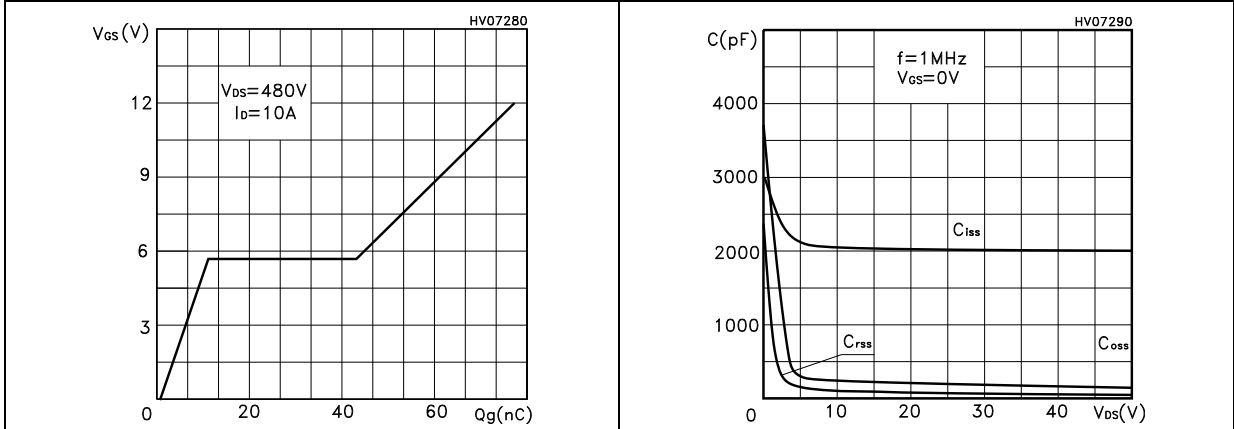


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

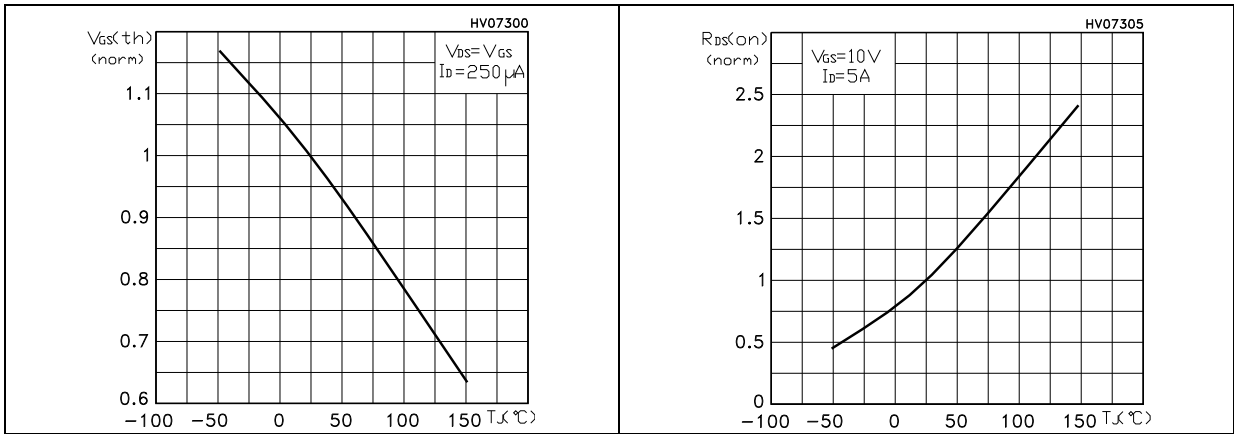


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized $B_{V_{DSS}}$ vs temperature

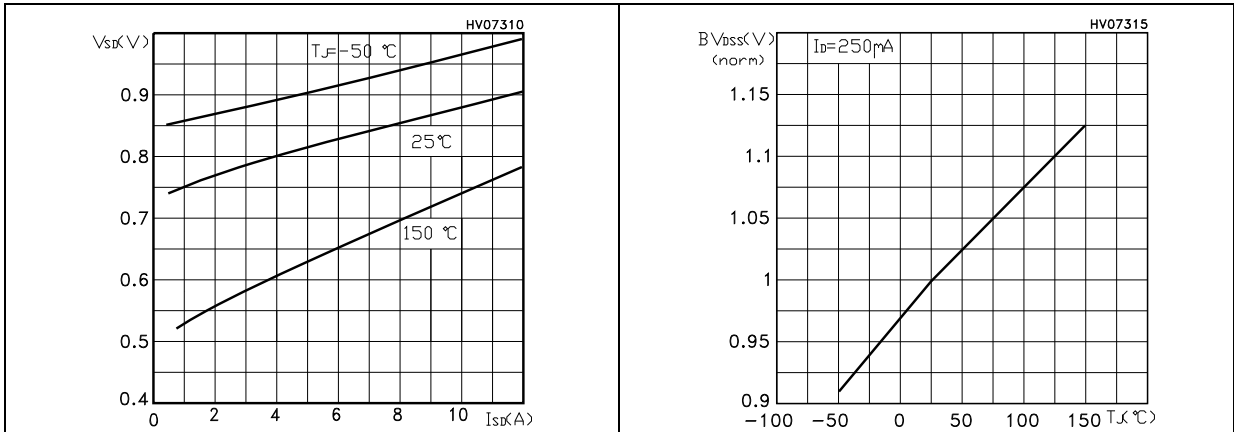
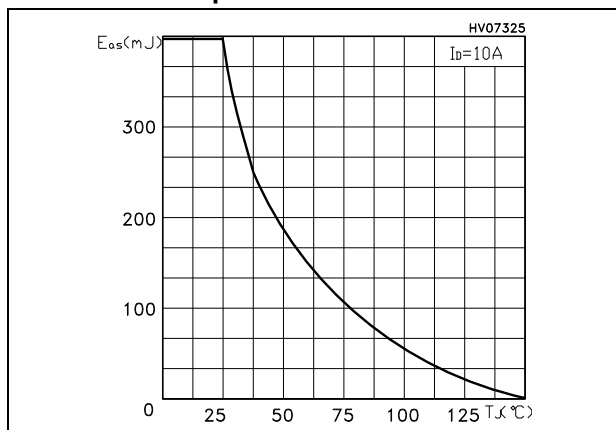


Figure 14. Maximum avalanche energy vs temperature



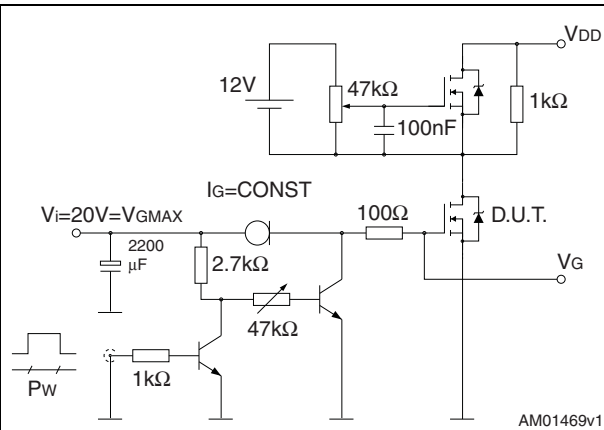
3 Test circuits

Figure 15. Switching times test circuit for resistive load



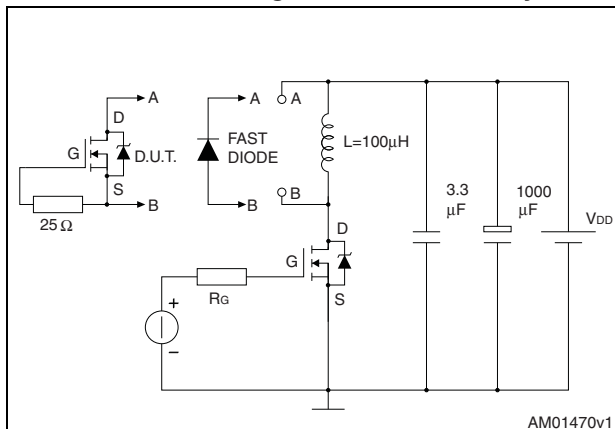
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Figure 16. Gate charge test circuit



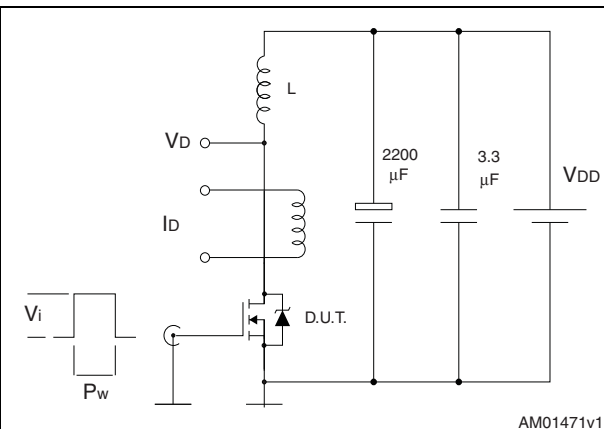
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Figure 17. Test circuit for inductive load switching and diode recovery times



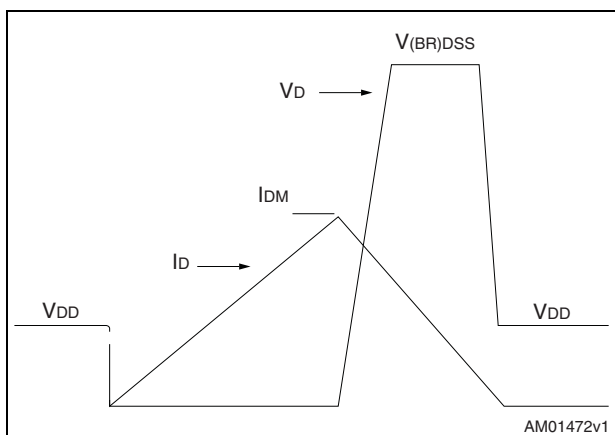
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Figure 18. Unclamped inductive load test circuit



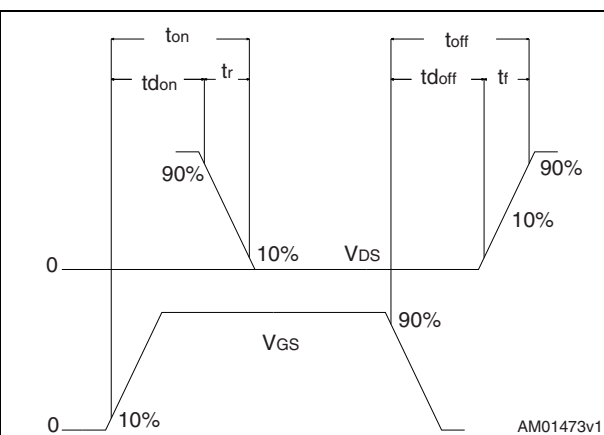
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Figure 19. Unclamped inductive waveform



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Figure 20. Switching time waveform



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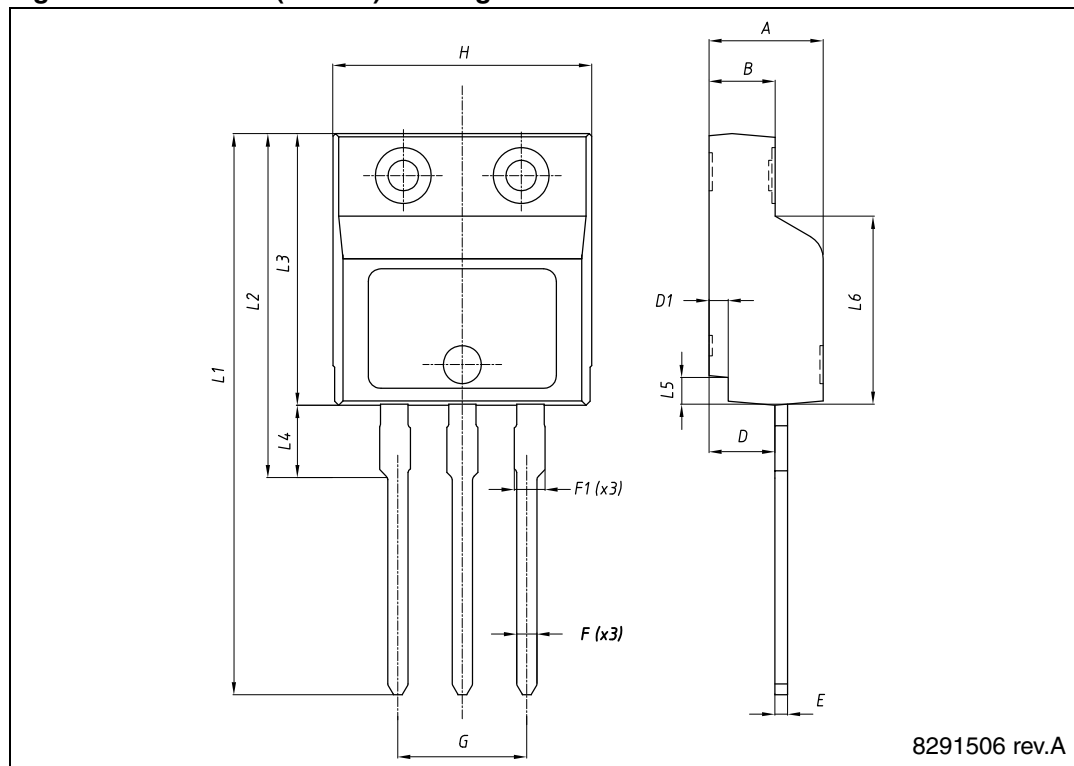
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 10. I²PAKFP (TO-281) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
B	2.50		2.70
D	2.50		2.75
D1	0.65		0.85
E	0.45		0.70
F	0.75		1.00
F1			1.20
G	4.95	-	5.20
H	10.00		10.40
L1	21.00		23.00
L2	13.20		14.10
L3	10.55		10.85
L4	2.70		3.20
L5	0.85		1.25
L6	7.30		7.50

Figure 21. I²PAKFP (TO-281) drawing



5 Revision history

Table 11. Document revision history

Date	Revision	Changes
06-Jul-2011	1	First release.
07-Nov-2011	2	<i>Figure 2: Safe operating area</i> and <i>Figure 3: Thermal impedance</i> have been added.
20-Mar-2012	3	Document status promoted from preliminary data to production data. The package name has been updated.

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